This research involved studies of the magnetic properties of multilayered magnetic films and high quality thin. Both ultra high vacuum sputtering and molecular beam epitaxy techniques were utilized to prepare the films. Both electrical transport and mageto-optic effects were used to measure the magnetic properties of the films. The primary focus during this year was to develop high quality trilayers consisting of a magnetic layer, nonmagnetic layer, and a magnetic layer. These structures are being developed to determine the scattering origin of the giant magnetoresistance phenomena. In addition, other investigations included the determination of the temperature dependence of the magnetic anisotropy energies of epitaxial iron films, the magnetization dynamics of thin films, and the general transport properties of multilayers. The transport effort utilized multilayers of magnetic and nonmagnetic metals to study the interfacial scattering. The combination of a magnetic and nonmagnetic metal in this work facilitates the origin of the scattering by use of the anisotropic magnetoresistance.
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I. Statement of Work

This research program was directed at developing new models for a more fundamental understanding of magnetism and to investigate new magnetic phenomena such as the recent discovery of exchange coupled multilayers. The research focused on the use of advanced thin film preparation techniques to prepare high quality multilayered and single layer thin films. Much of the research utilized magneto-transport techniques to probe the magnetic properties of the magnetic films. In particular, the research has investigated the magnetic properties of bcc Co, the role of interfacial disorder in the recently discovered exchange coupling in magnetic multilayers and the giant magnetoresistance phenomena, the magnetization process and related dynamics in high quality films and a continuing investigation of the temperature dependence of the anisotropy energies in epitaxial iron films. The experimental investigative tools include magnetotransport in magnetic fields up to 10 tesla, SQUID magnetometry, and magnetooptic magnetometry used for simultaneous detection of magnetization parallel and perpendicular to the applied magnetic fields.

II. Accomplished Research

During the first year of this grant, two of the senior graduate students received their Ph.D.'s and some of their work is yet to be published. These students have been followed by three relatively new graduate students. As one might expect, the more junior students have not yet reached a high level of productivity. In any event, as a mechanism of describing this research, we will list and discuss the publications which have been either published, submitted for publication, or are currently in draft form. For completeness, those works which were not yet published by the end of the last report for the previous grant will be included.


This publication utilizes the technique we developed using magneto-optics to provide a simultaneous measure of the magnetization in two orthogonal directions in a magnetic film. This work focuses on (100) oriented iron films. These films differ from those we investigated earlier in that they do not possess all three primary three crystallographic directions in the film planes but instead only have the <100> and the <110> directions. The lack of the <111> direction completely alters the magnetization process. The (100) films appear to magnetize in a much more uniform manner. The data taken on these films was modeled with a uniform rotation of the magnetization direction. In the modeling, we were able to determine the anisotropy energies and, as expected, show that prior to a jump in the magnetization direction that the magnetization process is dominated by wall formation.

Of current interest in the physics community is the recently discovered giant magnetoresistance (GMR) effect and the long range coupling (LRC) in magnetic/nonmagnetic multilayers. At the present time, a phenomenological model exists for the GMR (using the same physics as for the Stern-Gerlach experiment using spin projection) but a detailed understanding is lacking. This paper which we submitted to the ICM compares the GMR to the anisotropic magnetoresistance (AMR) in systems which exhibit the GMR. We have analyzed the data with a model of Fert which first was used to describe the AMR as a two-current system and in different limits, the GMR. The result of the work is that the AMR and the GMR are BOTH consistent with this two current model of Fert.


We are continuing to pursue an understanding of the magnetization processes in thin films; this work is a continuation of that effort. In this work, the angular dependence of the magnetization process in Fe/GaAs (100) thin films was studied using the magneto-optical Kerr effects. The actual experiments relied upon the simultaneous measurements of the magnetization both parallel and perpendicular to the applied field using the technique we pioneered and reported on previously (Florczak and Dahlberg, J. Appl. Phys. 67, 7520 (1990). In the present work, we find the magnetization proceeds in two steps which require the nucleation of 90° domain walls in the films. The interesting point is that there is an angular dependence to the second nucleation process but, within experimental error, not the second. At the present we don't understand this phenomena but are attempting model using the model developed in C. above and a nucleation model of Arrott.


In this work, we have used two models to understand the transport in multilayered systems; the parallel resistor model and the alloy model. In H. above only the parallel resistor model was used. In this work, both the parallel resistor model and the alloy model were used to describe the transport properties of these films. Again, as in H., the result is that the simple models are lacking and measures of the AMR and the resistivity do not provide sufficient information to improve the models, i.e., we are left with too many adjustable parameters. We do not mean to trivialize the research in
H. and I. as they both are necessary as first steps in this exciting research area and both provide direction for the future work which is described below.


In this work we determine the value of the anisotropic magnetoresistance (AMR) as a function temperature for the principal crystallographic directions, the (100), (110), and (111), in epitaxial iron films. Averages of the AMR along the different directions is equivalent to the value measured in polycrystalline samples. It is found that for the current applied along the (100) directions in the films with thicknesses over 17.5 nm, it is difficult to saturate the AMR. The reason for this lack of saturation is undetermined. From measurements of the magnetization, this large magnetoresistance can only be associated with a very small percentage of the magnetization of the films, on the order of one percent. One possibility is that for the thicker films, pinning of the magnetization at the interface creates a domain wall and there is a giant magnetoresistance phenomena associated with the wall. For the other directions it is likely that the current is parallel or nearly parallel to the wall and so this behavior does not occur.


A number of workers have measured giant magnetoresistance (GMR) samples with rather low values of the GMR. An accurate determination of the GMR in these samples requires one to separate the anisotropic magnetoresistance (AMR) contribution from the measured magnetotransport properties. In this work, we develop a technique which accurately separates the AMR and the GMR in measurements. This technique is applicable for the case where the AMR is unaffected by the GMR scattering phenomena or, at least, in the case of small GMR. The general applicability of this technique will be determined by a detailed understanding of the high resistance GMR state.

G. "Dependence of the Anisotropic Magnetoresistance on Aspect Ratio in Cobalt Films," by Mark Tondra, Brad Miller, and E. Dan Dahlberg, abstract submitted for consideration of publication.

The anisotropic magnetoresistance (AMR) is defined as the asymmetry in the electrical transport with the current parallel and perpendicular to the magnetization of the sample. This work shows that in large area samples, say a square for instance, with inline contacts, the measured AMR is less than the intrinsic AMR of the material. Essentially what occurs is that at the injection point for the current, the current spreads to fill the space available to minimize the current density. This means that the current does not flow exactly parallel to the line of contacts but has components perpendicular also. As the width of the sample increases with fixed contact separation the measured AMR decreases.
At fixed width, the measured AMR decreases as the distance between the like polarity (either positive or negative) current and voltage contacts is reduced. This work impacts both basic research designs and device work. In particular, it shows that for experiments on the spin valve effect (SVE), that large square samples with either contacts in the corners or inline contacts reduce any potential error in the SVE determination arising from the AMR; the SVE is an isotropic magnetoresistance phenomena and is thus unaffected by the aspect ratio of the sample other than the conventional geometrical factors.
III. Invited Talks for Research Accomplishments


IV. Personnel

A. Florczak, J.T., PhD in Physics received in 1992 (recipient of IBM predoctoral fellowship, 89-90) and currently employed at 3M Corp.
B. Chen, Y.-J., PhD in Physics received in 1992, currently employed with Nonvolatile Electronics, Inc.
C. Tondra, M., Ph.D. Graduate Student in Physics.
D. Miller, B., Ph.D. Graduate Student in Physics.
E. Engle, E., Ph.D. Graduate Student in Physics.
F. Kaufmann, D., Undergraduate Student in Physics, Graduated Summa Cum Laude, currently in the Carlson School of Management.
G. K. Sigsbee, K. Undergraduate Student in Physics, Graduated Summa Cum Laude, Currently in graduate school in physics at the University of Minnesota.
H. Sankar, S., Undergraduate Student in Physics.